# MEMORY **Un-buffered** $1 \text{ M} \times 64 \text{ BIT}$ SYNCHRONOUS DYNAMIC RAM SO-DIMM

# MB8501S064AC-100/-84/-67

## 168-pin, 1 Clock, 1-bank, based on 1 $M \times 16$ BIT SDRAMs with SPD

### DESCRIPTION

The Fujitsu MB8501 S064AB is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of four MB811161622A devices which organized as two banks of 1 M × 16 bits and a 2 K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8501S064AB features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8501S064AB is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for workstations, PCs, laser printers, and other applications where a simple interface is needed.

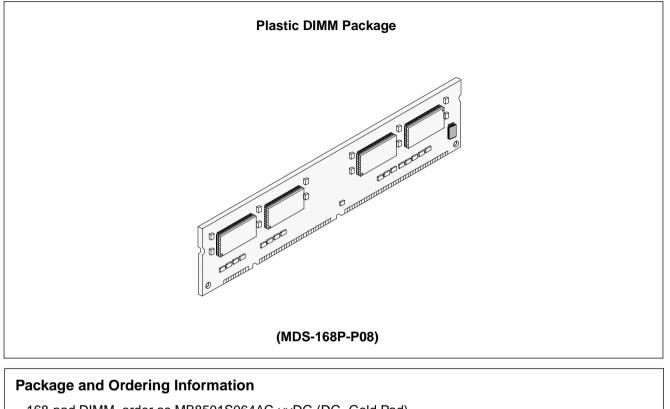
## PRODUCT LINE & FEATURES

Para	ameter	MB8501S064AC-100	MB8501S064AC-84	MB8501S064AC-67
Clock Frequency		100 MHz max.	84 MHz max.	67 MHz max.
Burst Mode Cycle Time		10 ns max. (CL = 3) 15 ns max. (CL = 2)	12 ns max. (CL = 3) 17 ns max. (CL = 2)	15 ns max. (CL = 3) 20 ns max. (CL = 2)
RAS Access Time		54 ns max.	56 ns max.	60 ns max.
CAS Access Time	CAS Access Time		26 ns max.	30 ns max.
Output Valid from Clock		8.5 ns max. (CL = 3) 9 ns max. (CL = 2)	8.5 ns max. (CL = 3) 9 ns max. (CL = 2)	9 ns max. (CL = 3) 10 ns max. (CL = 2)
Power Burst Mode		1944 mW max.	1800 mW max.	1620 mW max.
Dissipation	Power Down Mode		28.8 mW max.	

- Un-buffered 168-pin DIMM Socket Type (Lead pitch: 1.27 mm)
- Conformed to JEDEC Standard (1 CLK)
- Organization: 1,048,576 words × 64 bits
- 3.3 V ±0.3 V Supply Voltage
- All input/output LVTTL compatible

- 2048 Refresh Cycle every 32.8 ms
- Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Memory : MB811171622A (1 M×16, 2-bank)×4 pcs. Serial Presence Detect (SPD) with Serial EEPROM
  - Module size: 1.0" (height)  $\times$  5.25" (length)  $\times$  0.110" (thick)

### PACKAGE



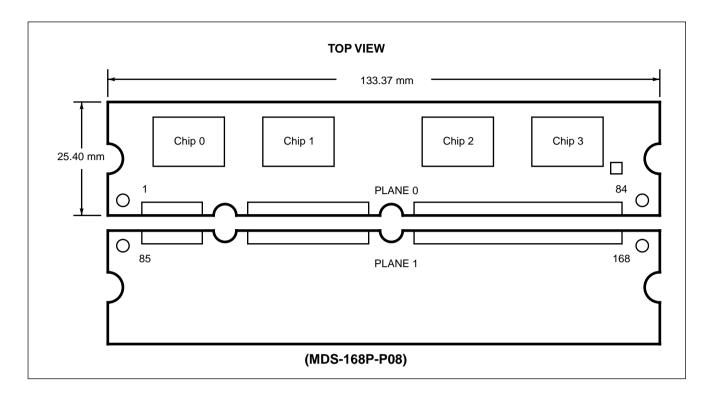
- 168-pad DIMM, order as MB8501S064AC-xxDG (DG=Gold Pad)

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## MB8501S064AC-100/-84/-67

## ■ PIN ASSIGNMENTS

Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name
1	Vss	29	DQMB <sub>1</sub>	57	DQ18	85	Vss	113	DQMB₅	141	DQ50
2	DQ <sub>0</sub>	30	$\overline{CS}_0$	58	DQ <sub>19</sub>	86	DQ32	114	N.C.	142	DQ <sub>51</sub>
3	DQ <sub>1</sub>	31	N.C.	59	Vcc	87	DQ33	115	RAS	143	Vcc
4	DQ <sub>2</sub>	32	Vss	60	DQ20	88	DQ <sub>34</sub>	116	Vss	144	DQ <sub>52</sub>
5	DQ₃	33	Ao	61	N.C.	89	DQ <sub>35</sub>	117	A <sub>1</sub>	145	N.C.
6	Vcc	34	A2	62	N.C.	90	Vcc	118	Аз	146	N.C.
7	DQ4	35	A4	63	N.C.	91	DQ <sub>36</sub>	119	A <sub>5</sub>	147	N.C.
8	DQ₅	36	A6	64	Vss	92	DQ <sub>37</sub>	120	A7	148	Vss
9	DQ <sub>6</sub>	37	A <sub>8</sub>	65	DQ <sub>21</sub>	93	DQ38	121	A9	149	DQ <sub>53</sub>
10	DQ7	38	A10	66	DQ22	94	DQ39	122	A11	150	DQ <sub>54</sub>
11	DQ8	39	N.C.	67	DQ <sub>23</sub>	95	DQ <sub>40</sub>	123	N.C.	151	DQ55
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss
13	DQ <sub>9</sub>	41	Vcc	69	DQ <sub>24</sub>	97	DQ <sub>41</sub>	125	N.C.	153	DQ <sub>56</sub>
14	DQ <sub>10</sub>	42	CLK <sub>0</sub>	70	DQ <sub>25</sub>	98	DQ <sub>42</sub>	126	N.C.	154	DQ <sub>57</sub>
15	DQ <sub>11</sub>	43	Vss	71	DQ <sub>26</sub>	99	DQ <sub>43</sub>	127	Vss	155	DQ <sub>58</sub>
16	DQ12	44	N.C.	72	DQ <sub>27</sub>	100	DQ44	128	CKE	156	DQ59
17	DQ <sub>13</sub>	45	$\overline{CS}_2$	73	Vcc	101	DQ <sub>45</sub>	129	N.C.	157	Vcc
18	Vcc	46	DQMB <sub>2</sub>	74	DQ <sub>28</sub>	102	Vcc	130	DQMB <sub>6</sub>	158	DQ60
19	DQ <sub>14</sub>	47	DQMB <sub>3</sub>	75	DQ29	103	DQ <sub>46</sub>	131	DQMB7	159	DQ <sub>61</sub>
20	DQ <sub>15</sub>	48	N.C.	76	DQ30	104	DQ <sub>47</sub>	132	N.C.	160	DQ <sub>62</sub>
21	N.C.	49	Vcc	77	DQ <sub>31</sub>	105	N.C.	133	Vcc	161	DQ <sub>63</sub>
22	N.C.	50	N.C.	78	Vss	106	N.C.	134	N.C.	162	Vss
23	Vss	51	N.C.	79	N.C.	107	Vss	135	N.C.	163	N.C.
24	N.C.	52	N.C.	80	N.C.	108	N.C.	136	N.C.	164	N.C.
25	N.C.	53	N.C.	81	N.C.	109	N.C.	137	N.C.	165	SA <sub>0</sub>
26	Vcc	54	Vss	82	SDA	110	Vcc	138	Vss	166	SA1
27	WE	55	DQ <sub>16</sub>	83	SCL	111	CAS	139	DQ <sub>48</sub>	167	SA <sub>2</sub>
28	DQMB <sub>0</sub>	56	DQ <sub>17</sub>	84	Vcc	112	DQMB <sub>4</sub>	140	DQ <sub>49</sub>	168	Vcc



## ■ PIN DESCRIPTION

Symbol	I/O	Function	Symbol	I/O	Function
A <sub>0</sub> to A <sub>11</sub>	I	Address Input	DQ <sub>0</sub> to DQ <sub>63</sub>		Data Input/Data Output
RAS	I	Row Address Strobe	Vcc	I/O	Power Supply (+3.3 V)
CAS	I	Column Address Strobe	Vss	-	Ground (0 V)
WE	I	Write Enable	N.C.	-	No Connection
DQMB <sub>0</sub> to DQMB <sub>7</sub>	I	Data (DQ) Mask	SA <sub>0</sub> to SA <sub>2</sub>	-	Serial PD Address Input
CLK₀	I	Clock Input	SCL	I	Serial PD Clock
СКЕ	I	Clock Enable	SDA	I/O	Serial PD Address/Data Input/Output
$\overline{CS}_0, \overline{CS}_2$	I	Chip Select			

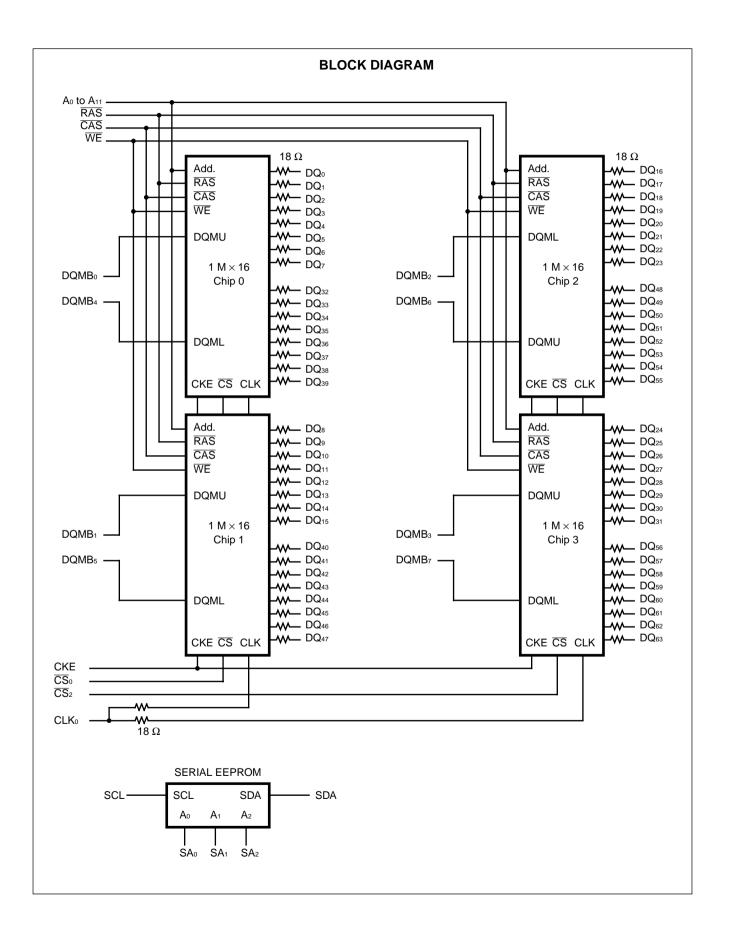
### SERIAL-PD INFORMATION

Byte	Function Described		Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
0	Defines Number of Bytes Written into	128 Byte	1	0	0	0	0	0	0	0
	Serial Memory at Module Manufacture	-								
1	Total Number of Bytes of SPD Memory	256 Byte	0	0	0	0	1	0	0	0
2 3	Fundamental Memory Type	SDRAM	0	0	0	0	0	1	0	0
3	Number of Row Addresses	11	0	0	0	0	1	0	1	1
4	Number of Column Addresses	8	0	0	0	0	1	0	0	0
5	Number of Module Banks	1 bank	0	0	0	0	0	0	0	1
6	Data Width	64 bit	0	1	0	0	0	0	0	0
7	Data Width (Continuation)	+0	0	0	0	0	0	0	0	0
8	Interface Type	LVTTL	0	0	0	0	0	0	0	1
9	SDRAM Cycle Time	10 ns	1	0	1	0	0	0	0	0
		12 ns	1	1	0	0	0	0	0	0
		15 ns	1	1	1	1	0	0	0	0
10	SDRAM Access from Clock	8.5 ns	1	0	0	0	0	1	0	1
		9 ns	1	0	0	1	0	0	0	0
11	DIMM Configuration Type	Non-Parity	0	0	0	0	0	0	0	0
12	Refresh Rate/Type	Self, Norm	1	0	0	0	0	0	0	0
13	SDRAM Module Attributes	UN-Buffer	0	0	0	0	0	0	0	0
14	SDRAM Device Attributes	(*)	0	0	0	0	0	1	1	0
15	Minimum Clock Delay Back to Back	1 Cycle	0	0	0	0	0	0	0	1
	Random Column Address			-	-	-				
16	Burst Lengths Supported	1, 2, 4, 8	0	0	0	0	1	1	1	1
17	Number of Banks on Each SDRAM Device	2 bank	0	0	0	0	0	0	1	0
18	CAS Latency	2, 3	0	0	0	0	0	1	1	0
19	CS Latency	0	0	0	0	0	0	0	0	
20	Write Latency	0	0	0	0	0	0	0	0	1
21 to 31	Reserved for Future Offerings	—	0	0	0	0	0	0	0	0
32 to 63	Superset Information	—	0	0	0	0	0	0	0	0
64 to 125	Manufacturer's Information		0	0	0	0	0	0	0	0
126	Intel Specification Frequency	66 MHz	0	1	1	0	0	1	1	0
127	Intel Specification CAS Latency	2, 3	0	0	0	0	0	1	1	0
128+	Unused Storage Locations	_	-	_	-	-	_	_	-	-

**Note:** Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

(\*) Byte 14 : SDRAM Device Attributes

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
TBD	TBD	TBD	TBD	Supported Single Write/ Burst Read	Supported Precharge All	Supported Auto- Precharge	Supported Early RAS Precharge
0	0	0	0	0	1	1	0



## ■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Baramatar	Symbol	Va	Value			
Parameter	Symbol	Min.	Max.	Unit		
Supply Voltage*	Vcc	-0.5	+4.6	V		
Input Voltage*	Vin	-0.5	+4.6	V		
Output Voltage*	Vout	-0.5	+4.6	V		
Storage Temperature	Тѕтс	-55	+125	°C		
Power Dissipation	PD		5.2	W		
Output Current (D.C.)	Ιουτ	-50	+50	mA		

\* : Voltages referenced to Vss (= 0 V)

**WARNING:** Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

## ■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol		Unit		
Farameter	Notes	Symbol	Min.	Тур.	Max.	Unit
Supply Voltage	*1	Vcc	3.0	3.3	3.6	V
Supply voltage	I	Vss	0	0	0	V
Input High Voltage, All Inputs	*1	Vін	2.0		Vcc +0.5	V
Input Low Voltage, All Inputs	*1, 2	VIL	-0.5		0.8	V
Ambient Temperature		TA	0	_	+70	°C

\*1. Voltages referenced to Vss (= 0 V)

\*2.  $V_{\mathbb{L}}$  (min) = -1.5 V AC (Pulse Width  $\leq$  5 ns)

**WARNING:** Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses , operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

## ■ CAPACITANCE

	+3.3 V, f = 1 MHz, TA	$= +25^{\circ}C$
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Parame	or	Symbol	Va	lue	Unit
Falalle	lei	Symbol	Min.	Max.	Unit
	A <sub>0</sub> to A <sub>11</sub>	CIN1	—	30	pF
	RAS, CAS, WE	CIN2	—	29	pF
	$\overline{CS}_0, \overline{CS}_2$	Сімз	—	15	pF
	CKE	CIN4	—	29	pF
Input Capacitance		CIN5	—	29	pF
	DQMB <sub>0</sub> to DQMB <sub>7</sub>	CIN6	—	11	pF
	SCL	CSCL	—	6	pF
	SA0, SA1, SA2	CSA	—	5	pF
	SDA	CSDA	—	6	pF
Input/Output Capacitance	DQ <sub>0</sub> to DQ <sub>63</sub>	CDQ		11	pF

## ■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

Denemoter	Nataa		Ourseland	O a malitia m	Va	lue	11
Parameter	Notes		Symbol	Condition	Min.	Max.	Unit
		MB8501S064AC-100		No Burst;		340	mA
		MB8501S064AC-84	Icc1s	tcκ = min t <sub>RC</sub> = min		320	mA
Operating Current (Average Power	*2	MB8501S064AC-67		One Bank Active		300	mA
Supply Current)		MB8501S064AC-100		No Burst;		520	mA
		MB8501S064AC-84	Ісс1р	tск = min trc = min		480	mA
		MB8501S064AC-67	-	All Banks Active		440	mA
Precharge Standby Current (Power	*0		Ісс2р	CKE = V⊩, tcĸ = min All Banks Idle		8	mA
Supply Current)			Ісс2N	CKE = V⊮, tcк = min All Banks Idle		120	mA
Active Standby Current (Power *2 Supply Current)			Іссзр	CKE = V⊫, tcк = min Any Bank Active		120	mA
			Іссзи	CKE = V⊮, tcк = min Any Bank Active		200	mA
Burst Mode Current		MB8501S064AC-100			_	540	mA
(Average Power	*2	MB8501S064AC-84	Icc4	tcк = min	_	500	mA
Supply Current)		MB8501S064AC-67				460	mA
Auto-refresh Current		MB8501S064AC-100		Auto Refresh		440	mA
(Average Power	*2	MB8501S064AC-84	Icc5	tск = min t <sub>RC</sub> = min		400	mA
Supply Current)		MB8501S064AC-67		t <sub>RRD</sub> = min		360	mA
Self-refresh Current (Average Power Supply	Currer	nt)	Icc6	tcк = VIL		8	mA
Input Leakage Current (All Inputs)		lı (l)	$\begin{array}{l} 0 \ V \leq V_{IN} \leq V_{CC} \\ \text{All other pins not} \\ \text{under test} = 0 \ V \\ 3.0 \ V \leq V_{CC} \leq 3.6 \ V \end{array}$	-30	30	μA	
Output Leakage Current		IO (L)	$\begin{array}{l} Output \mbox{ is disabled (Hi-Z)} \\ 0 \ V \leq V_{OUT} \leq V_{CC} \\ 3.0 \ V \leq V_{CC} \leq 3.6 \ V \end{array}$	-10	10	μA	
LVTTL Output High Voltage	*1		Vон	lон = −2.0 mA	2.4	_	V
LVTTL Output Low Voltage	*1		Vol	IoL = +2.0 mA		0.4	V

**Notes:** \*1. Voltages referenced to Vss (= 0 V)

\*2. Icc depends on the output termination, load conditions, clock cycle rate and signal clock rate. The specified values are obtained with the output open and no termination register.

\*3. An initial pause (DESL on NOP) of 200 μs is required after power-on followed by a minimum of eight Auto-Refresh cycles.

\*4. DC characteristics is the Serial PD standby state ( $V_{IN} = GND$  or  $V_{CC}$ ).

## ■ AC CHARACTERISTICS

## (1) BASE CHARACTERISTICS

## (At recommended operating conditions unless otherwise noted.)

No.	Parameter Notes		Symbol		S064AC 00		S064AC 34	MB8501S064AC -67		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
1	Clock Period	CL = 3	4	10	—	12		15	_	ns
I	Clock Period	CL = 2	tск	15		17		20	_	ns
2	Clock High Time		tсн	4		4		4	_	ns
3	Clock Low Time		tc∟	4		4		4	—	ns
4	CS Set Up Time		tsc	3		3		3	_	ns
5	CS Hold Time		tнc	1		1		1	_	ns
6	Input Set Up Time		tsi	3		3		3	—	ns
7	Input Hold Time		tнı	1		1		1	—	ns
8	Data Input Set Up Time		tsid	3		3		3	—	ns
9	Data Input Hold Time		tнid	1	—	1		1	—	ns
	Output Valid	CL = 3			8.5	_	8.5		9	
10	from Clock *1, *2 (tcLK = min)	CL = 2	tac		9	_	9	_	10	ns
11	Output in Low-Z		tolz	3		3		3	_	ns
12	Output in High-Z *3		tонz	3		3		3	_	ns
13	Output Hold Time		tон	3	_	3		3	_	ns
14	Time between Refresh		tref		32.8	_	32.8		32.8	ms
15	Transition Time		tτ	0.5	2	0.5	2	0.5	2	ns
16	Power Down Exit Time		<b>t</b> PDE	3	_	4	_	5	_	ns

No.	Parameter	Notes	Symbol	MB8501S064AC -100		MB8501S064AC -84		MB8501S064AC -67		Unit
			-	Min.	Max.	Min.	Max.	Min	Max.	
1	RAS Cycle Time	*4	<b>t</b> RC	90		100		110		ns
2	RAS Access Time	*5	<b>t</b> RAC		54		56	—	60	ns
3	CAS Access Time	*6, *9	tcac		24		26		30	ns
4	RAS Precharge Time		<b>t</b> RP	30		35	—	40	—	ns
5	RAS Active Time		tras	60	100000	65	100000	70	100000	ns
6	RAS to CAS Delay Time	*7	<b>t</b> RCD	30	—	30	_	30	—	ns
7	Write Recovery Time		<b>t</b> wr	10	_	12	_	15	—	ns
8	Write Precharge Time		<b>t</b> RWL	10		12	_	15	—	ns
9	RAS to CAS Bank Active Delay Time		<b>t</b> rrd	30	_	30	_	30	_	ns

### (2) BASE VALUES FOR CLOCK COUNT/LATENCY

### (3) CLOCK COUNT FORMULA (\*8)

 $Clock \ge \frac{Base Value}{Clock Period}$  (Round off a whole number)

## (4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

				-	-	-	_
No.	Parameter		Symbol	MB8501S064AC -100	MB8501S064AC -84	MB8501S064AC -67	Unit
1	CKE to Clock Disable		Іске	1	1	1	Cycle
2	DQM to Output in High-Z		ldqz	2	2	2	Cycle
3	DQM to Input Data Delay		IDQD	0	0	0	Cycle
4	Last Output to Write Command Delay		lowd	2	2	2	Cycle
5	Write Command to Input Data Delay		ldwd	0	0	0	Cycle
6	Precharge to Output in High-Z Delay	CL = 3	la au	3	3	3	Cycle
		CL = 2	IROH	2	2	2	Cycle
7	Mode Register Access to Bank Active (min)		Imrd	2	2	2	Cycle
8	$\overline{CAS}$ to $\overline{CAS}$ Delay (min)		Ісср	1	1	1	Cycle
9	CAS Bank Delay (min)		Свр	1	1	1	Cycle

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## MB8501S064AC-100/-84/-67

- Notes: \*1. Assumes tRCD and tCAC are satisfied.
  - \*2. tac also specifies the access time at burst mode except for first access.
  - \*3. Specified where output buffer is no longer driven.
  - \*4. Actual clock count of trc (Irc) will be sum of clock count of tras (Iras) and trp (Irp).
  - \*5. trac is a reference value. Maximum value is obtained from the sum of trcd (min) and tcac (max).
  - \*6. Assumes trac and tac are satisfied.
  - \*7. Operation within the tRCD (min) ensures that tRAC can be met; if tRCD is greater than the specified tRCD (min), access time is determined by tCAC and tAC.
  - \*8. All base values are measured from the clock edge at the command input to the clock edge for the next command input.

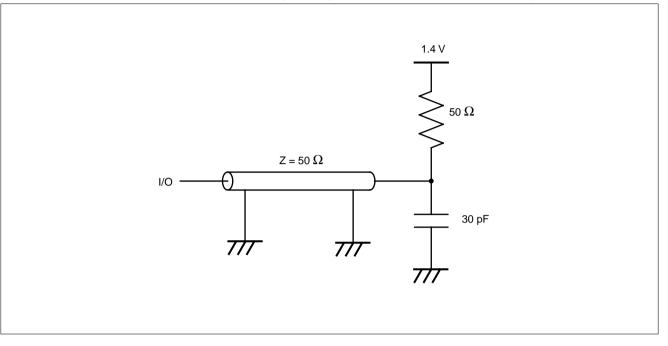
All clock counts are calculated by a simple formula:

clock count equals base value divided by clock period (round off to a whole number).

- \*9. The ICAC (CAS latency: CL) is programmed by the mode register.
- \*10. An initial pause ( DESL on NOP ) of 200 μs is required after power-up followed by a minimum of eight Auto-Refresh cycles.
- \*11. 1.4 V or V<sub>REF</sub> is the reference level for measuring timing of signals. Transition times are measured between V<sub>IH</sub> (min) and V<sub>IL</sub> (max).
- \*12. AC characteristics assume  $t_T = 1$  ns and 30 pF of capacitive load.

\*Source: See MB811171622A Data Sheet for details on the electricals.

## ■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



## ■ SERIAL PRESENCE DETECT(SPD) FUNCTION

#### 1. PIN DESCRIPTIONS

#### SCL (Serial Clock)

SCL input is used to clock all data input/output of SPD

#### SDA (Serial Data)

SDA is a common pin used for all data input/output of SPD. The SDA pull-up resistor is required due to the open-drain output.

#### SA<sub>0</sub>, SA<sub>1</sub>, SA<sub>2</sub> (Address)

Address inputs are used to set the least significant three bits of the eight bits slave address. The address inputs must be fixed to select a particular module and the fixed address of each module must be different each other.

#### 2. SPD OPERATIONS

#### **CLOCK and DATA CONVENTION**

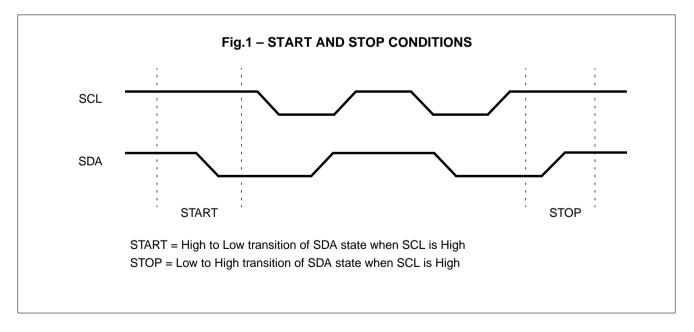
Data states on the SDA can change only during SCL=Low. SDA state changes during SCL=High are indicated start and stop conditions. Refer to Fig.1 below.

#### START CONDITION

All commands are preceded by a start condition, which is a transition of SDA state from High to Low when SCL=High. SPD will not respond to any command until this condition has been met.

#### **STOP CONDITION**

All read or write operation must be terminated by a stop condition, which is a transition of SDA state from Low to High when SCL=High. The stop condition is also used to make the SPD into the state of standby power mode after a read sequence.



#### ACKNOWLEDGE

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

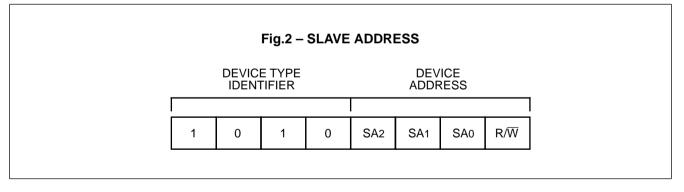
#### SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig.2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices–namely up to eight modules–on the bus. The eight addresses for eight SPD devices are defined by the state of the SA<sub>0</sub>, SA<sub>1</sub> and SA<sub>2</sub> inputs.

The last bit of the slave address defines the operation to be performed. When  $R/\overline{W}$  bit is "1", a read operation is selected, when  $R/\overline{W}$  bit is "0", a write operation is selected.

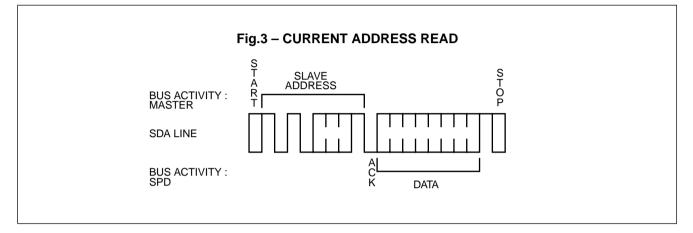
Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of SA<sub>0</sub>, SA<sub>1</sub>, and SA<sub>2</sub> inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the  $R/\overline{W}$  bit, the SPD will execute a read or write operation.



### 3. READ OPERATION

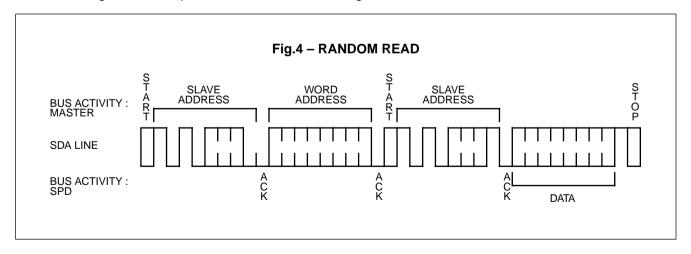
### **CURRENT ADDRESS READ**

Internally the SPD contains an address counter that maintains the address of the last data accessed, incremented by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the  $R/\overline{W}$  bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.3 for the sequence of address, acknowledge and data transfer.



#### **RANDOM READ**

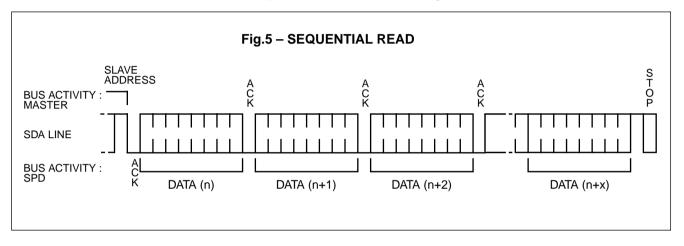
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the R/W bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the R/ $\overline{W}$  bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.4 for the sequence of address, acknowledge and data transfer.



#### SEQUENTIAL READ

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter "rolls over" to address 0 and the SPD continues to output data for each acknowledge received.



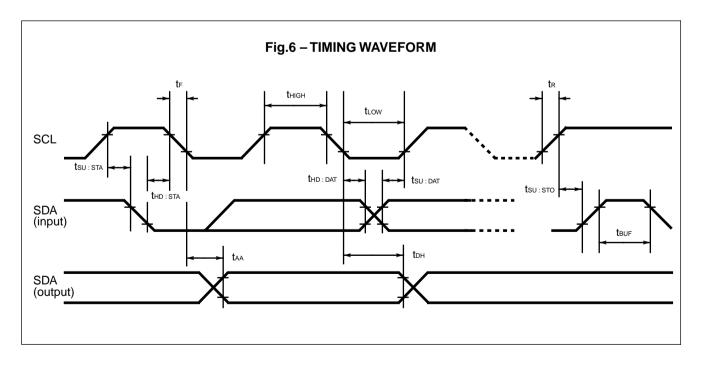
#### 4. DC CHARACTERISTICS

Parameter	Note	Symbol	Condition	Value		Unit
Falameter			Condition	Min.	Max.	Unit
Input Leakage Current		Sili	$0 \text{ V} \leq V_{\text{IN}} \leq V_{\text{CC}}$	-10	10	μA
Output Leakage Current		SILO	$0 \text{ V} \leq \text{V}_{\text{OUT}} \leq \text{V}_{\text{CC}}$	-10	10	μA
Output Low Voltage	*1	SVOL	IoL = 3.0 mA		0.4	V

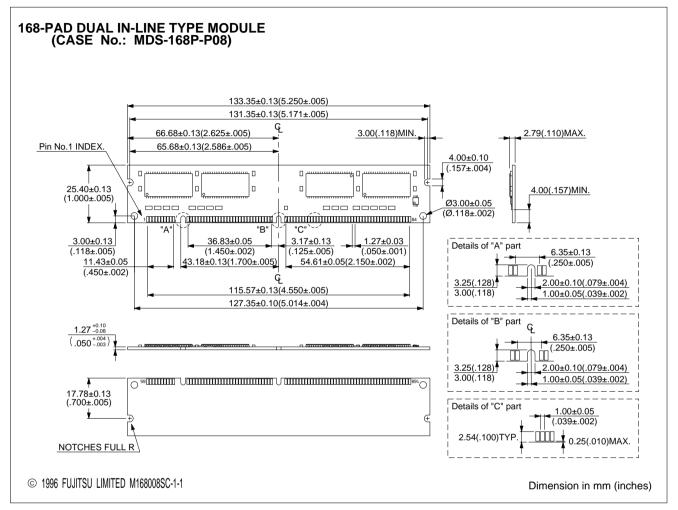
Note: \*1. Referenced to Vss.

### 5. AC CHARACTERISTICS

No.	Parameter	Symbol	Value		11:::4
	Farameter		Min.	Max.	- Unit
1	SCL Clock Frequency	fscL	0	100	KHz
2	Noise Suppression Time Constant at SCL, SDA Inputs	Tı		100	ns
3	SCL Low to SDA Data Out Valid	taa		3.5	μs
4	Time the Bus Must Be Free Before a New Transmission Can Start	tBUF	4.7	_	μs
5	Start Condition Hold Time	thd:sta	4.0		μs
6	Clock Low Period	tLow	4.7		μs
7	Clock High Period	tніgн	4.0	_	μs
8	Start Condition Set Up Time	tsu:sta	4.7		μs
9	Data In Hold Time	thd:dat	0		μs
10	Data In Set Up Time	tsu:dat	250		ns
11	SDA and SCL Rise Time	tR	_	1	μs
12	SDA and SCL Fall Time	t⊧	_	300	ns
13	Stop Condition Set Up Time	tsu:sto	4.7	_	μs
14	Data Out Hold Time	tон	100	_	ns
15	Write Cycle Time	twr	—	15	ms



#### PACKAGE DIMENSION



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